

Dual P-channel MOSFET

ELM544953A-N

<http://www.elm-tech.com>

■ General description

ELM544953A-N uses advanced trench technology to provide excellent $R_{ds(on)}$, low gate charge and low gate threshold voltage.

■ Features

- $V_{ds} = -30V$
- $I_d = -5.4A$
- $R_{ds(on)} = 50m\Omega$ ($V_{gs} = -10V$)
- $R_{ds(on)} = 75m\Omega$ ($V_{gs} = -4.5V$)

■ Maximum absolute ratings

$T_a = 25^\circ C$. Unless otherwise noted.

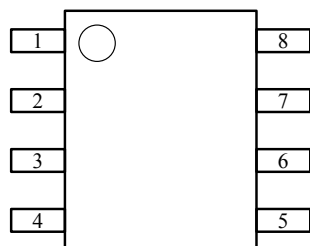
Parameter	Symbol	Limit	Unit
Drain-source voltage	V_{ds}	-30	V
Gate-source voltage	V_{gs}	± 20	V
Continuous drain current	I_d	$T_a = 25^\circ C$	-5.4
		$T_a = 70^\circ C$	-4.2
Pulsed drain current	I_{dm}	-30	A
Power dissipation	P_d	$T_c = 25^\circ C$	2.8
		$T_c = 70^\circ C$	1.8
Junction and storage temperature range	T_j, T_{stg}	- 55 to 150	$^\circ C$

■ Thermal characteristics

Parameter	Symbol	Typ.	Max.	Unit
Thermal resistance junction-to-ambient	$R_{\theta ja}$		62.5	$^\circ C/W$

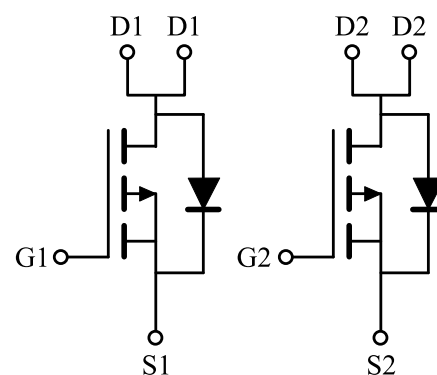
■ Pin configuration

SOP-8(TOP VIEW)



Pin No.	Pin name
1	SOURCE1
2	GATE1
3	SOURCE2
4	GATE2
5	DRAIN2
6	DRAIN2
7	DRAIN1
8	DRAIN1

■ Circuit



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■Electrical characteristics

Ta=25°C. Unless otherwise noted.

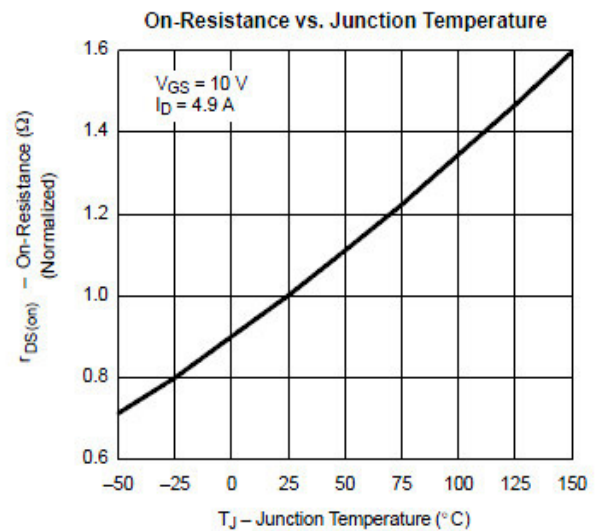
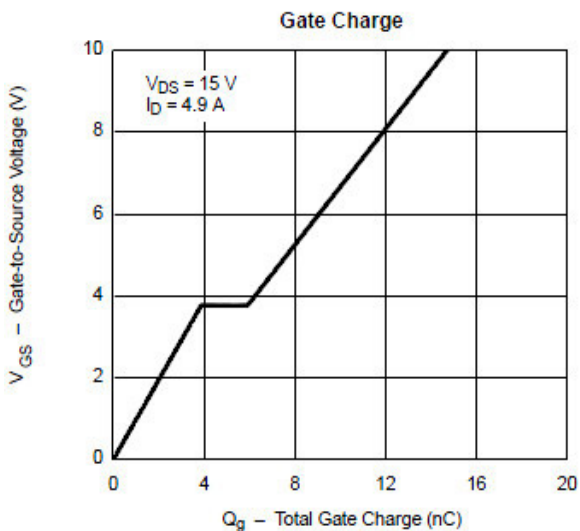
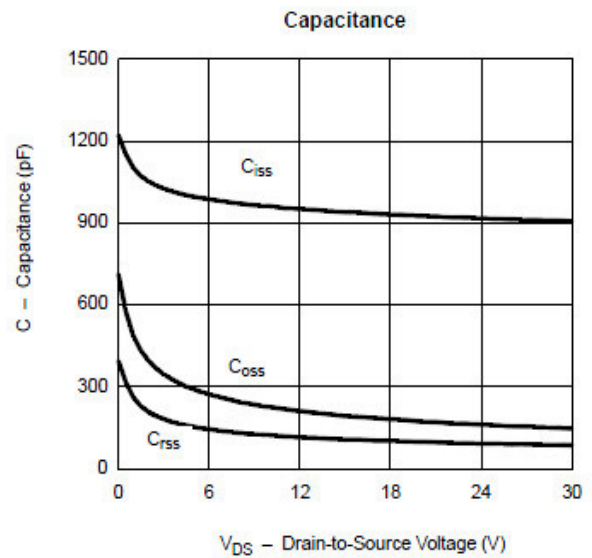
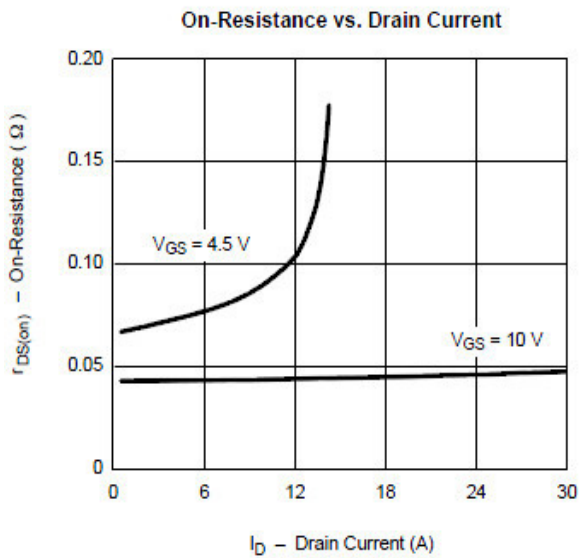
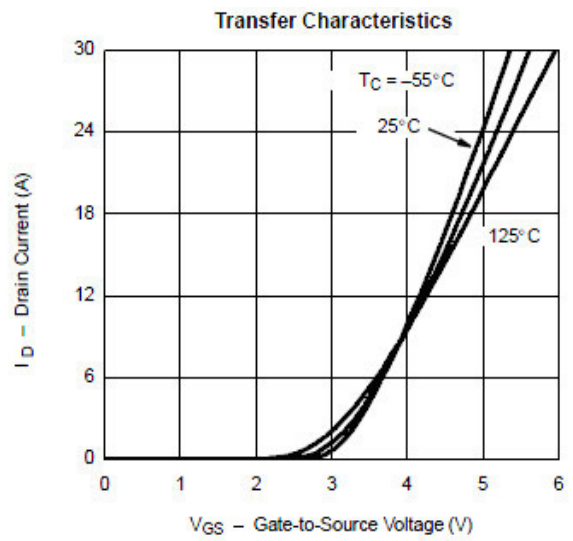
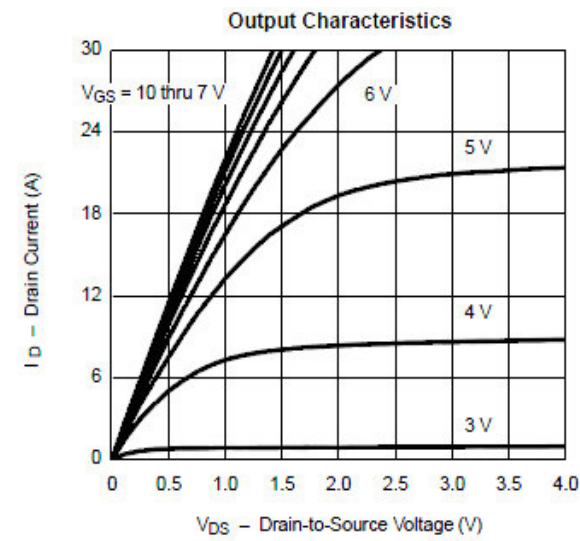
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-source breakdown voltage	BVdss	Id=-250μA, Vgs=0V	-30			V
Zero gate voltage drain current	Idss	Vds=-24V, Vgs=0V Ta=85°C			-1	μA
					-30	
Gate-body leakage current	Igss	Vds=0V, Vgs=±20V			±100	nA
Gate threshold voltage	Vgs(th)	Vds=Vgs, Id=-250μA	-1.0		-2.5	V
On state drain current	Id(on)	Vgs=-10V, Vds=-5V	-25			A
Static drain-source on-resistance	Rds(on)	Vgs=-10V, Id=-5.4A		35	50	mΩ
		Vgs=-4.5V, Id=-4.2A		56	75	
Forward transconductance	Gfs	Vds=-10V, Id=-4.9A		10		S
Diode forward voltage	Vsd	Is=-1.7A, Vgs=0V		-0.8	-1.3	V
Max. body-diode continuous current	Is				-1.7	A
DYNAMIC PARAMETERS						
Input capacitance	Ciss	Vgs=0V, Vds=-15V, f=1MHz		500		pF
Output capacitance	Coss			100		pF
Reverse transfer capacitance	Crss			55		pF
SWITCHING PARAMETERS						
Total gate charge	Qg	Vgs=-10V, Vds=-15V, Id=-5A		10.0	18.0	nC
Gate-source charge	Qgs			1.6		nC
Gate-drain charge	Qgd			3.0		nC
Turn-on delay time	td(on)	Vgs=-10V, Vds=-15V RL=15Ω, Id=-1.0A Rgen=6Ω		8	18	ns
Turn-on rise time	tr			8	18	ns
Turn-off delay time	td(off)			25	50	ns
Turn-off fall time	tf			25	35	ns

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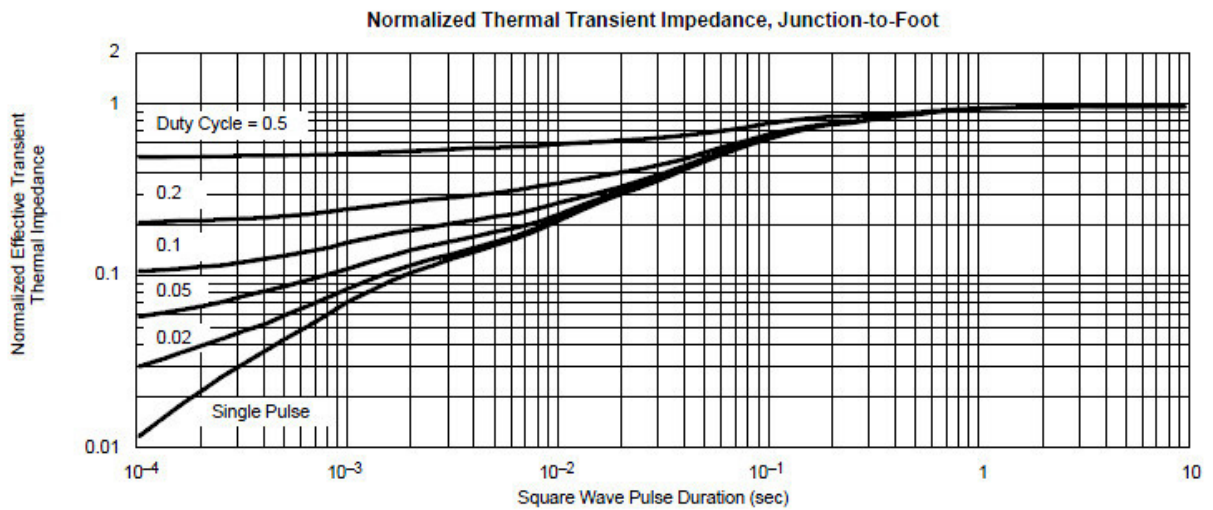
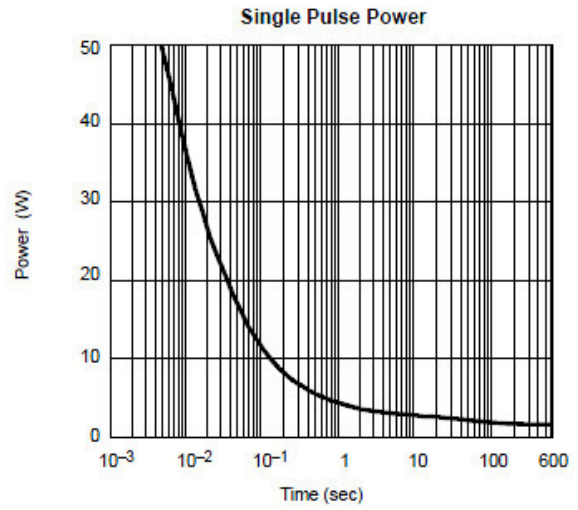
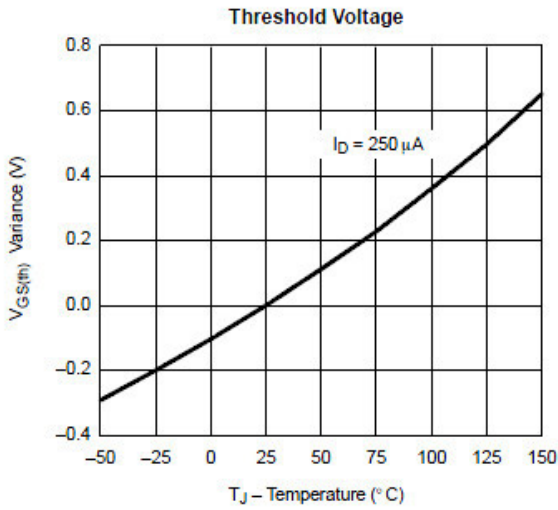
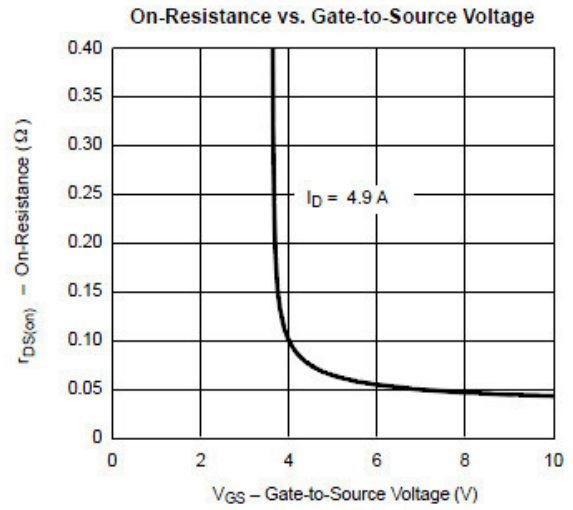
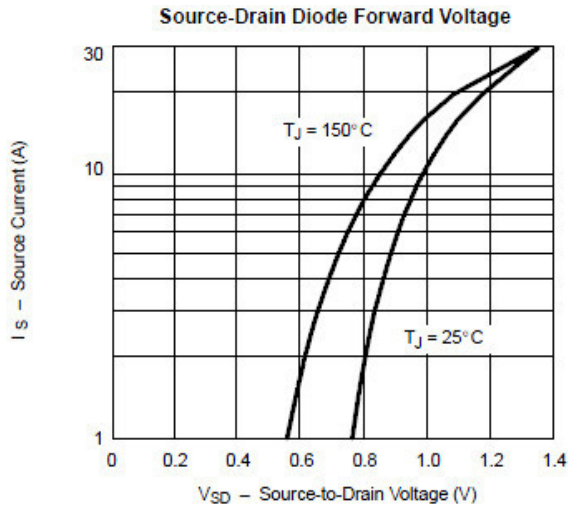
■ Typical electrical and thermal characteristics



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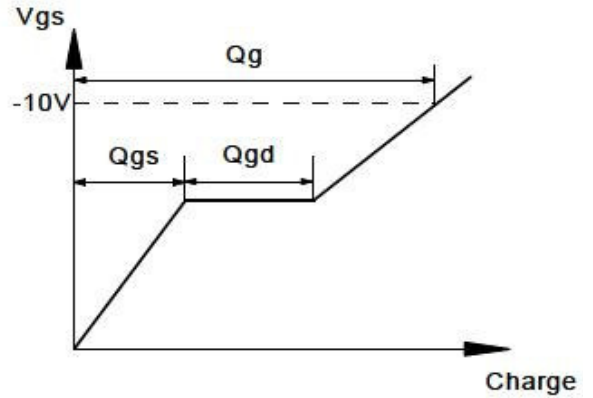
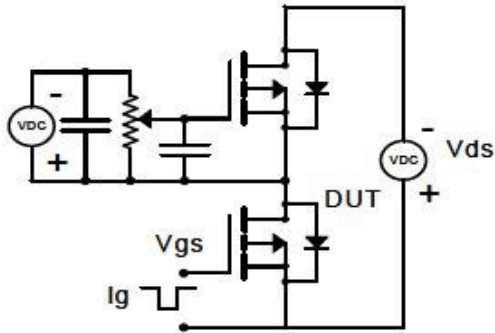
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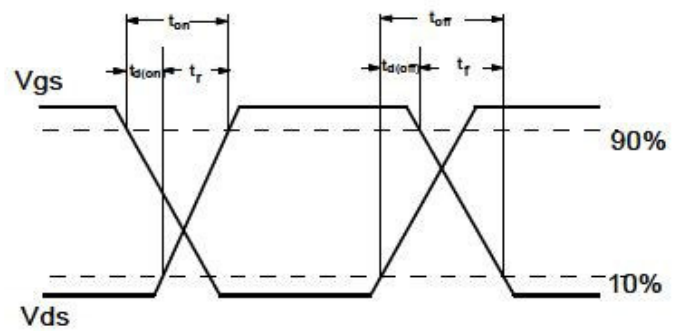
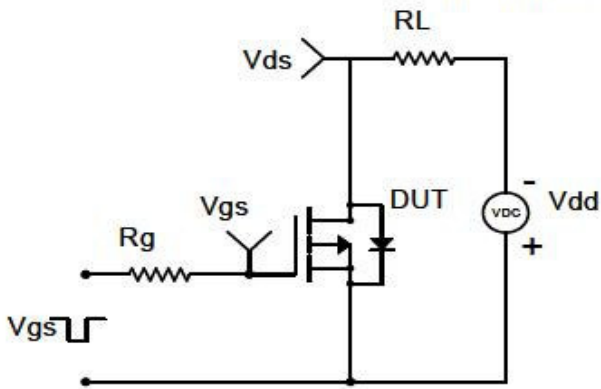
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■ Test circuit and waveform

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

